

Silicon NPN Power Transistors

2SD1459

DESCRIPTION

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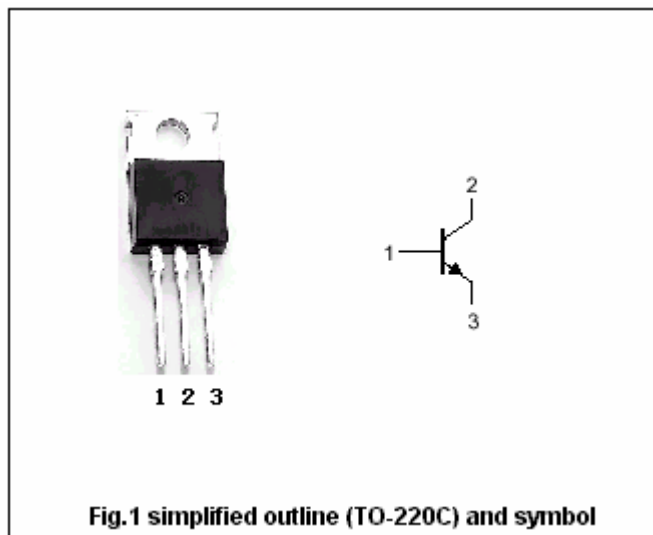
- With TO-220 package
- High allowable collector dissipation.
- Complement to type 2SB1037

APPLICATIONS

- Color TV vertical output application
- Sound output application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_{CM}	Collector current-peak		3.0	A
P_C	Collector power dissipation		2.0	W
		$T_C=25^\circ\text{C}$	30	
T_j	Junction temperature		175	℃
T_{stg}	Storage temperature		-55~175	℃

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CHARACTERISTICS

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 $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 10\text{mA}$; $I_B = 0$	150			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 0.5\text{A}$, $I_B = 50\text{mA}$			1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = 0.5\text{A}$, $I_B = 50\text{mA}$			1.2	V
I_{CBO}	Collector cut-offcurrent	$V_{CB} = 120\text{V}$; $I_E = 0$			10	μA
I_{EBO}	Emitter cut-offcurrent	$V_{EB} = 5\text{V}$; $I_C = 0$			10	μA
h_{FE}	DC current gain	$I_C = 0.3\text{A}$; $V_{CE} = 5\text{V}$	70		200	
f_T	Transition frequency	$I_C = 0.1\text{A}$; $V_{CE} = 5\text{V}$		8		MHz

◆ h_{FE} classifications

Q	R
70-140	100-200

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